



High-reliability discrete products
and engineering services since 1977

2N6546-2N6547

NPN SILICON POWER TRANSISTORS

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Ratings	Symbol	2N6546	2N6547	Unit
Collector-emitter voltage	V_{CE}	300	400	V
Collector-emitter voltage	V_{CEV}	650	850	V
Emitter-base voltage	V_{EBO}		9.0	V
Collector current – continuous Peak ⁽¹⁾	I_C		15 30	A
Base current – continuous	I_B		10	A
Emitter current – continuous Peak	I_E I_{EM}		25 50	A
Total power dissipation @ $T_c = 25^\circ\text{C}$ Derate above 25°C	P_T		175 1.0	W W/ $^\circ\text{C}$
Operating junction and storage temperature range	T_J, T_{stg}		-65 to +200	$^\circ\text{C}$
THERMAL CHARACTERISTICS				
Maximum thermal resistance, junction-to-case	R_{\thetaJC}		1.0	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-emitter sustaining voltage ⁽¹⁾ $I_C = 200\text{mA}, I_B = 0$	2N6546 2N6547	$V_{(BR)SUS}$	300 400	- -
Collector cutoff current $V_{CEV} = 650\text{V}, V_{BE(OFF)} = 1.5\text{V}$ $V_{CEV} = 850\text{V}, V_{BE(OFF)} = 1.5\text{V}$	2N6546 2N6547	I_{CEO}	- -	1.0 1.0
$V_{CEV} = 650\text{V}, V_{BE(OFF)} = 1.5\text{V}, T_c = 100^\circ\text{C}$ $V_{CEV} = 850\text{V}, V_{BE(OFF)} = 1.5\text{V}, T_c = 100^\circ\text{C}$	2N6546 2N6547		- -	4.0 4.0
Emitter cutoff current $V_{EB} = 8\text{V}, I_C = 0$	I_{EBO}	-	1.0	mA
ON-CHARACTERISTICS⁽¹⁾				
DC current gain $I_C = 5.0\text{A}, V_{CE} = 2.0\text{V}$ $I_C = 10\text{A}, V_{CE} = 2.0\text{V}$	h_{FE}	12 6.0	60 30	-
Collector-emitter saturation voltage $I_C = 10\text{A}, I_B = 2.0\text{A}$ $I_C = 15\text{A}, I_B = 3.0\text{A}$	$V_{CE(sat)}$	- -	1.5 5.0	V
Base-emitter saturation voltage $I_C = 10\text{A}, I_B = 2.0\text{A}$	$V_{BE(sat)}$	-	1.6	V
Current gain – bandwidth ⁽²⁾ $I_C = 500\text{mA}, V_{CE} = 10\text{V}, f = 1.0\text{MHz}$	f_T	6.0	35	MHz

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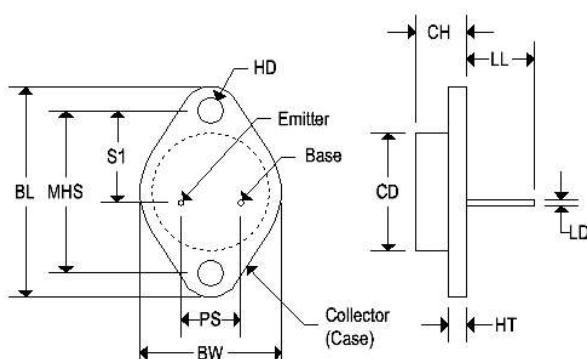
Characteristics		Symbol	Min.	Max.	Unit
SWITCHING CHARACTERISTICS					
Delay time		t _d	-	0.05	μs
Rise time	V _{CC} = 250V, I _C = 3.0A, I _{B1} = -I _{B2} = 0.6A,	t _r	-	1.0	μs
Storage time	t _p = 0.1ms, duty cycle ≤ 2.0%	T _s	-	4.0	μs
Fall time		t _f	-	0.8	μs

Note 1: Pulse test: pulse width = 300μs, duty cycle ≤ 2.0%.

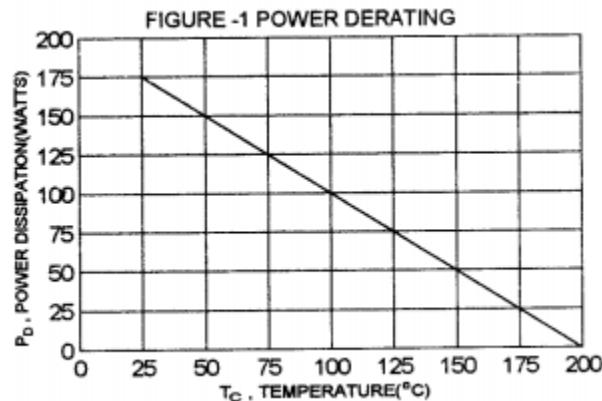
 Note 2: I_{HFE} × f_{test}

MECHANICAL CHARACTERISTICS

Case	TO-3
Marking	Alpha-numeric
Polarity	See below



	TO-3			
	Inches		Millimeters	
	Min	Max	Min	Max
CD	-	0.875	-	22.220
CH	0.250	0.335	6.350	8.510
HT	0.055	0.135	1.400	3.430
BW	-	1.050	-	26.670
HD	0.131	0.188	3.330	4.780
LD	0.038	0.043	0.970	1.090
LL	0.312	0.500	7.920	12.700
BL	1.550 REF		39.370 REF	
MHS	1.177	1.197	29.900	30.400
PS	0.420	0.440	10.670	11.180
S1	0.655	0.675	16.640	17.150



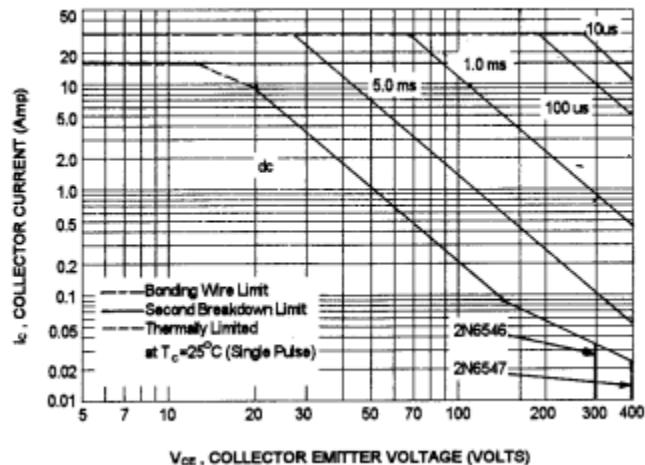


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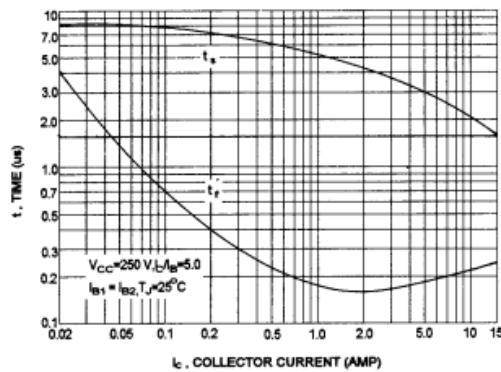
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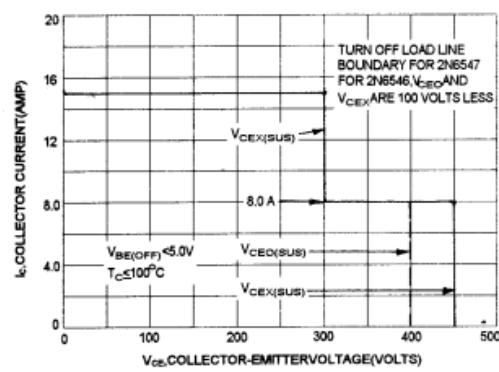
ACTIVE-REGION SAFE OPERATING AREA (SOA)



TURN-OFF TIME



REVERSE BIAS SAFE OPERATING AREA



TURN-ON TIME

